

# 74AHC2G126; 74AHCT2G126

Dual buffer/line driver; 3-state

Rev. 6 — 8 November 2011

Product data sheet

## 1. General description

The 74AHC2G126 and 74AHCT2G126 are high-speed Si-gate CMOS devices. They provide a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A LOW at nOE causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

## 2. Features and benefits

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E: exceeds 2000 V
  - ◆ MM JESD22-A115-A: exceeds 200 V
  - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC2G126DP 74AHCT2G126DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHC2G126DC 74AHCT2G126DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AHC2G126GD 74AHCT2G126GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2



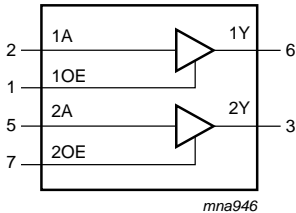
## 4. Marking

Table 2. Marking codes

Type number	Marking <sup>[1]</sup>
74AHC2G126DP	A26
74AHCT2G126DP	C26
74AHC2G126DC	A26
74AHCT2G126DC	C26
74AHC2G126GD	A26
74AHCT2G126GD	C26

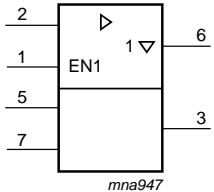
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram



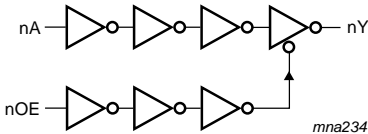
*mna946*

**Fig 1. Logic symbol**



*mna947*

**Fig 2. IEC logic symbol**

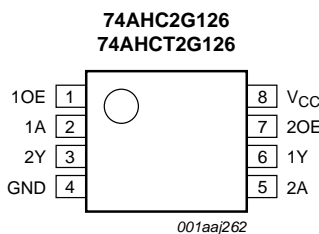


*mna234*

**Fig 3. Logic diagram (one buffer)**

## 6. Pinning information

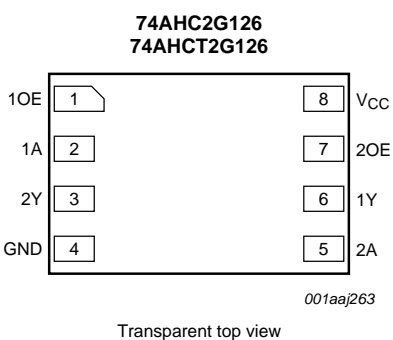
### 6.1 Pinning



**74AHC2G126**  
**74AHCT2G126**

*001aaJ262*

**Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)**



**74AHC2G126**  
**74AHCT2G126**

*001aaJ263*

Transparent top view

**Fig 5. Pin configuration SOT996-2 (XSON8U)**

## 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1OE, 2OE	1, 7	output enable input (active HIGH)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

Control	Input	Output
nOE	nA	nY
H	L	L
H	H	H
L	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
V <sub>I</sub>	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V	<sup>[1]</sup> -20	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	<sup>[1]</sup> -	±20	mA
I <sub>O</sub>	output current	-0.5 V < V <sub>O</sub> < V <sub>CC</sub> + 0.5 V	-	±25	mA
I <sub>CC</sub>	supply current		-	75	mA
I <sub>GND</sub>	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	<sup>[2]</sup> -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.  
 For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.  
 For XSON8U package: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G126			74AHCT2G126			Unit
			Min	Typ	Max	Min	Typ	Max	
$V_{CC}$	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
$V_I$	input voltage		0	-	5.5	0	-	5.5	V
$V_O$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	-	-	100	-	-	-	ns/V
		$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	-	-	20	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74AHC2G126</b>										
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 2.0 \text{ V}$	1.5	-	-	1.5	-	1.5	-	V
		$V_{CC} = 3.0 \text{ V}$	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 5.5 \text{ V}$	3.85	-	-	3.85	-	3.85	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
		$V_{CC} = 3.0 \text{ V}$	-	-	0.9	-	0.9	-	0.9	V
		$V_{CC} = 5.5 \text{ V}$	-	-	1.65	-	1.65	-	1.65	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_O = -50 \mu\text{A}$ ; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu\text{A}$ ; $V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu\text{A}$ ; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}$ ; $V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_O = -8.0 \text{ mA}$ ; $V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_O = 50 \mu\text{A}$ ; $V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu\text{A}$ ; $V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu\text{A}$ ; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}$ ; $V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}$ ; $V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
$I_{OZ}$	OFF-state output current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	$\mu\text{A}$
$I_I$	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to $5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	$\mu\text{A}$

**Table 7. Static characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$C_I$	input capacitance		-	1.5	10	-	10	-	10	pF
<b>74AHCT2G126</b>										
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
		$I_O = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -8.0 \text{ mA}$	3.94	-	-	3.8	-	3.70	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
		$I_O = 50 \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
$I_{OZ}$	OFF-state output current	$V_I = V_{CC} \text{ or } \text{GND}; V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	$\mu\text{A}$
$I_I$	input leakage current	$V_I = 5.5 \text{ V or } \text{GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC} \text{ or } \text{GND}; I_O = 0 \text{ A}; V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input pin; $V_I = 3.4 \text{ V};$ other inputs at $V_{CC} \text{ or } \text{GND}; I_O = 0 \text{ A}; V_{CC} = 5.5 \text{ V}$	-	-	1.35	-	1.5	-	1.5	mA
$C_I$	input capacitance		-	1.5	10	-	10	-	10	pF

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**  
 $GND = 0 \text{ V};$  for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74AHC2G126</b>										
$t_{pd}$	propagation delay	nA to nY; see <a href="#">Figure 6</a> <a href="#">[1]</a>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ <a href="#">[2]</a>								
		$C_L = 15 \text{ pF}$	-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		$C_L = 50 \text{ pF}$	-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ <a href="#">[3]</a>								
		$C_L = 50 \text{ pF}$	-	4.8	7.5	1.0	8.5	1.0	9.5	ns

**Table 8. Dynamic characteristics ...continued**GND = 0 V; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>en</sub>	enable time	nOE to nY; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V <a href="#">[2]</a>								
		C <sub>L</sub> = 15 pF	-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C <sub>L</sub> = 50 pF	-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	3.6	5.1	1.0	6.0	1.0	6.5	ns
t <sub>dis</sub>	disable time	nOE to nY; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V <a href="#">[2]</a>								
		C <sub>L</sub> = 15 pF	-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C <sub>L</sub> = 50 pF	-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	4.1	6.8	1.0	8.0	1.0	8.5	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; <a href="#">[4]</a>	-	10	-	-	-	-	-	pF
		C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>								
<b>74AHCT2G126</b>										
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 6</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
t <sub>en</sub>	enable time	nOE to nY; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	3.9	5.1	1.0	6.0	1.0	6.5	ns
t <sub>dis</sub>	disable time	nOE to nY; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	4.5	6.8	1.0	8.0	1.0	8.5	ns
t <sub>en</sub>	enable time	nOE to nY; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 50 pF	-	5.1	7.5	1.0	9.0	1.0	9.5	ns
t <sub>dis</sub>	disable time	nOE to nY; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 50 pF	-	6.1	8.8	1.0	10.0	1.0	11.0	ns

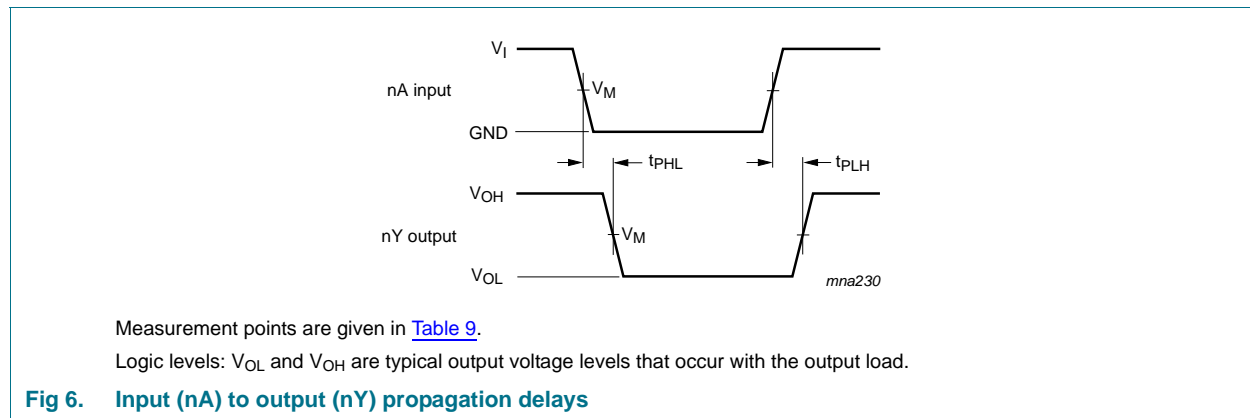
**Table 8. Dynamic characteristics ...continued**

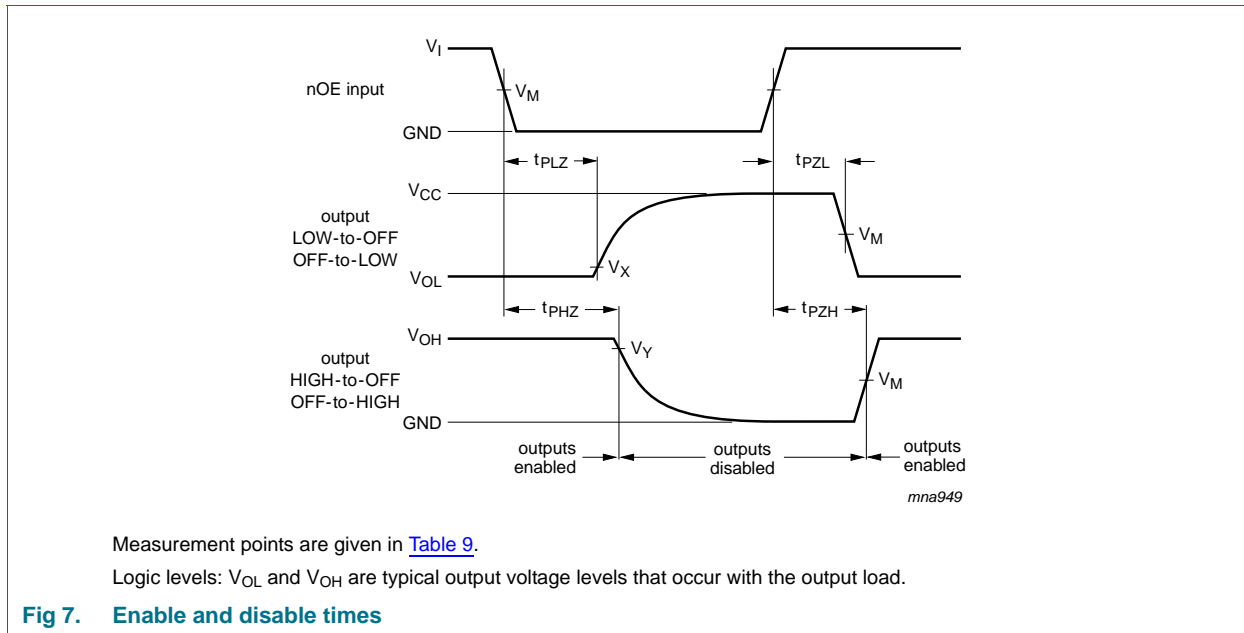
$GND = 0\text{ V}$ ; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$C_{PD}$	power dissipation capacitance	per buffer; $C_L = 50\text{ pF}$ ; $f_i = 1\text{ MHz}$ ; $V_i = GND\text{ to }V_{CC}$	[4] -	10	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .  
 $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .  
 $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .
- [2] Typical values are measured at  $V_{CC} = 3.3\text{ V}$ .
- [3] Typical values are measured at  $V_{CC} = 5.0\text{ V}$ .
- [4]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu\text{W}$ ).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:  
 $f_i$  = input frequency in MHz;  
 $f_o$  = output frequency in MHz;  
 $C_L$  = output load capacitance in pF;  
 $V_{CC}$  = supply voltage in Volts.

## 12. Waveforms

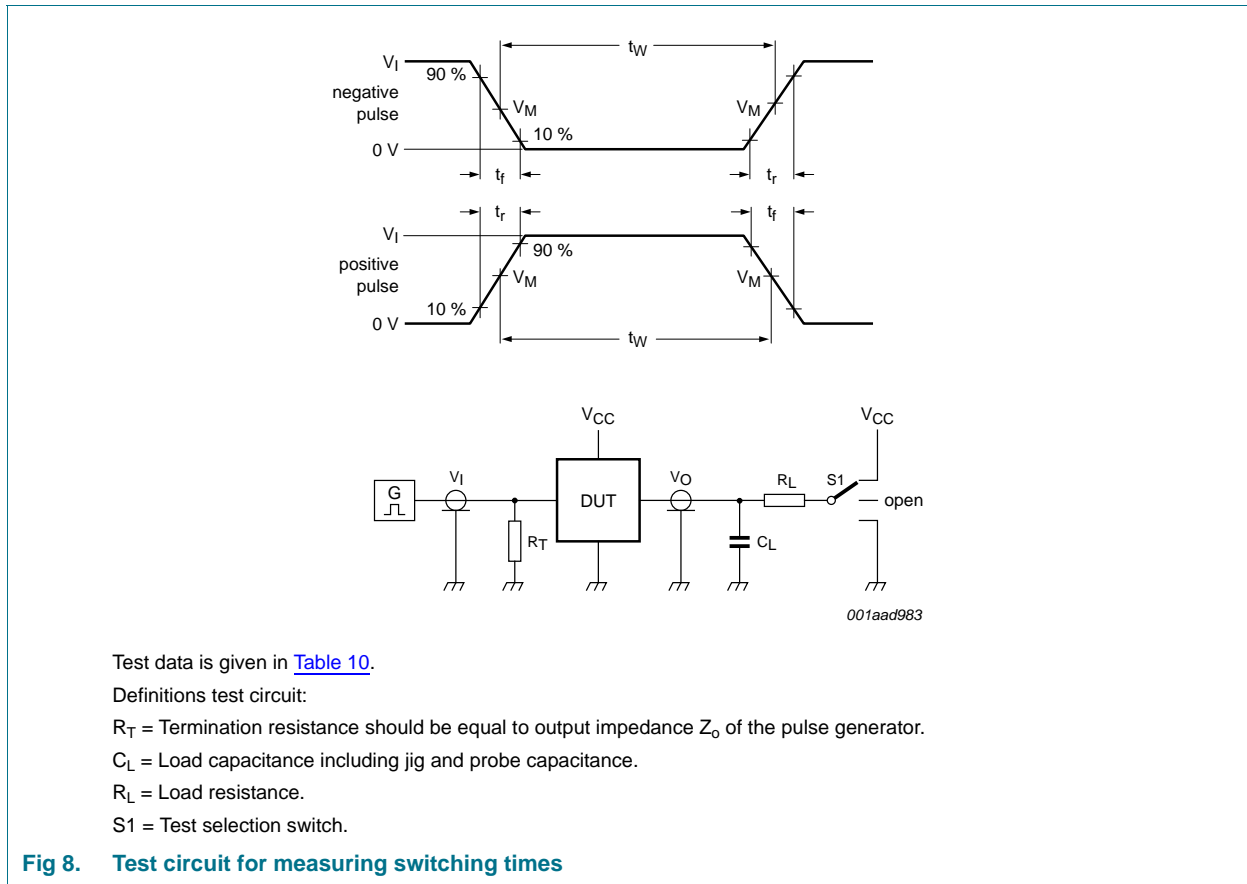




**Table 9. Measurement points**

Type	Input	Output		
	$V_M$	$V_M$	$V_X$	$V_Y$
74AHC2G126	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
74AHCT2G126	1.5 V	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$





**Table 10. Test data**

Type	Input		Load		S1 position		
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
74AHC2G126	$V_{CC}$	$\leq 3$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$
74AHCT2G126	3 V	$\leq 3$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$

## 13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

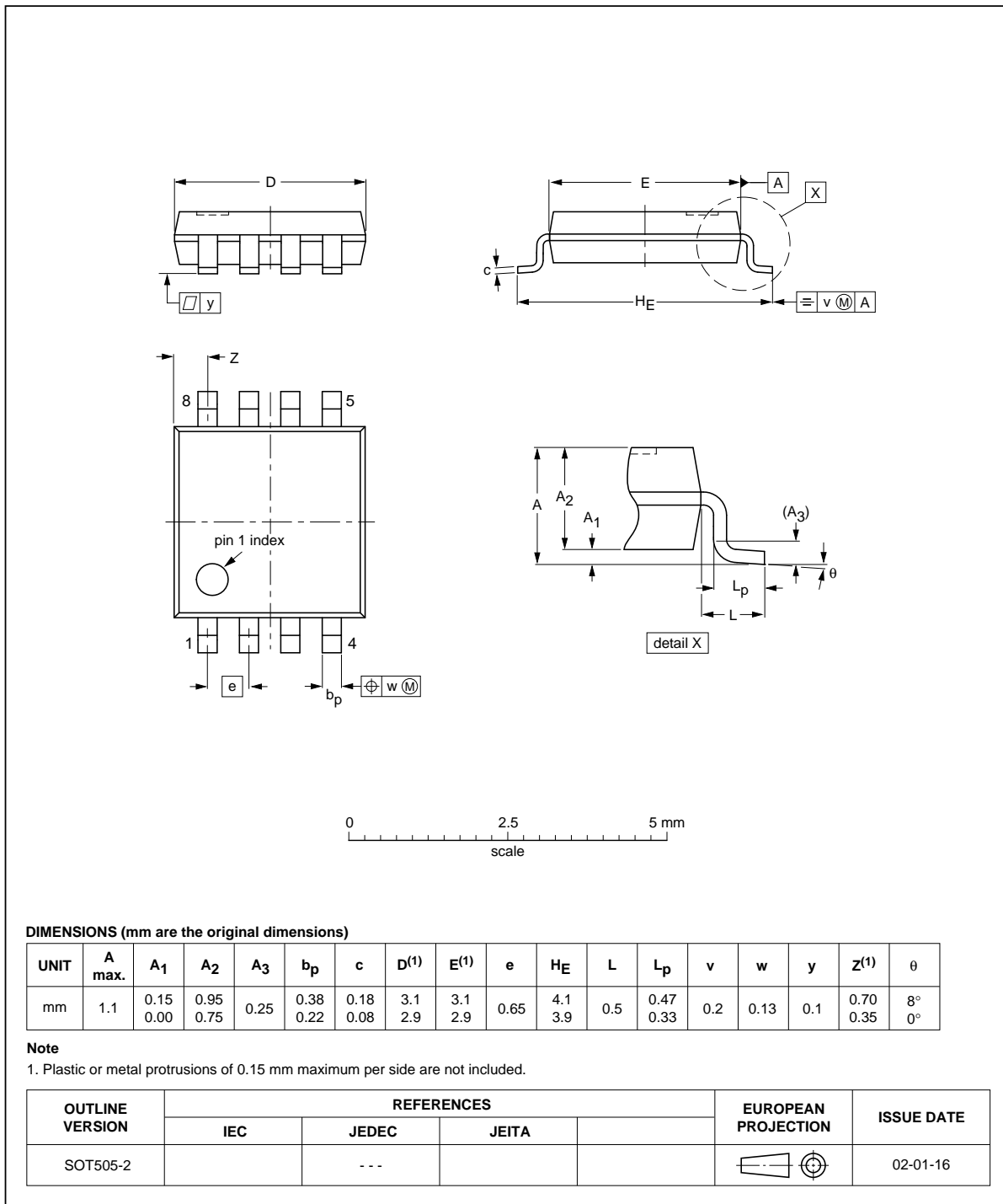


Fig 9. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

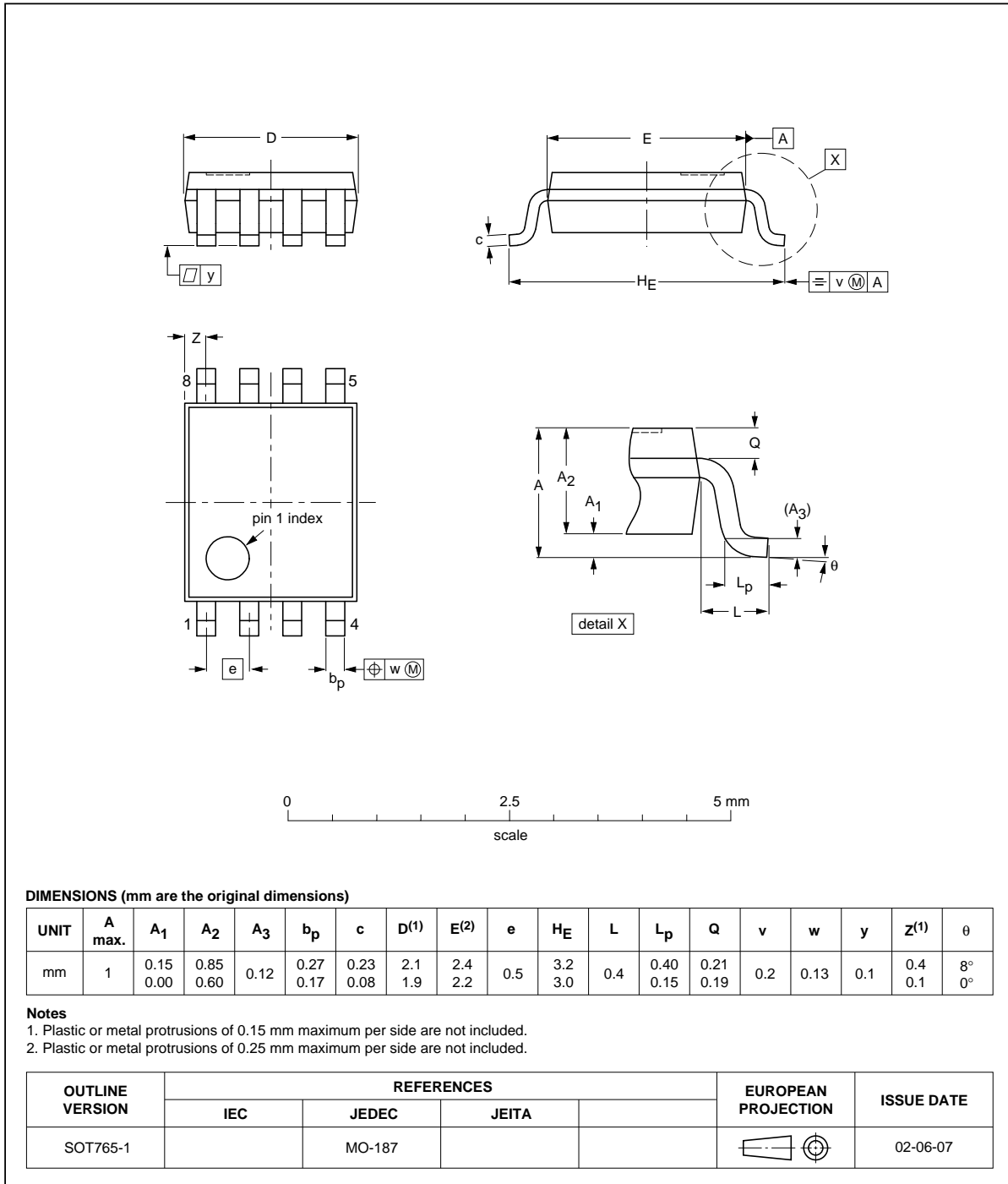


Fig 10. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

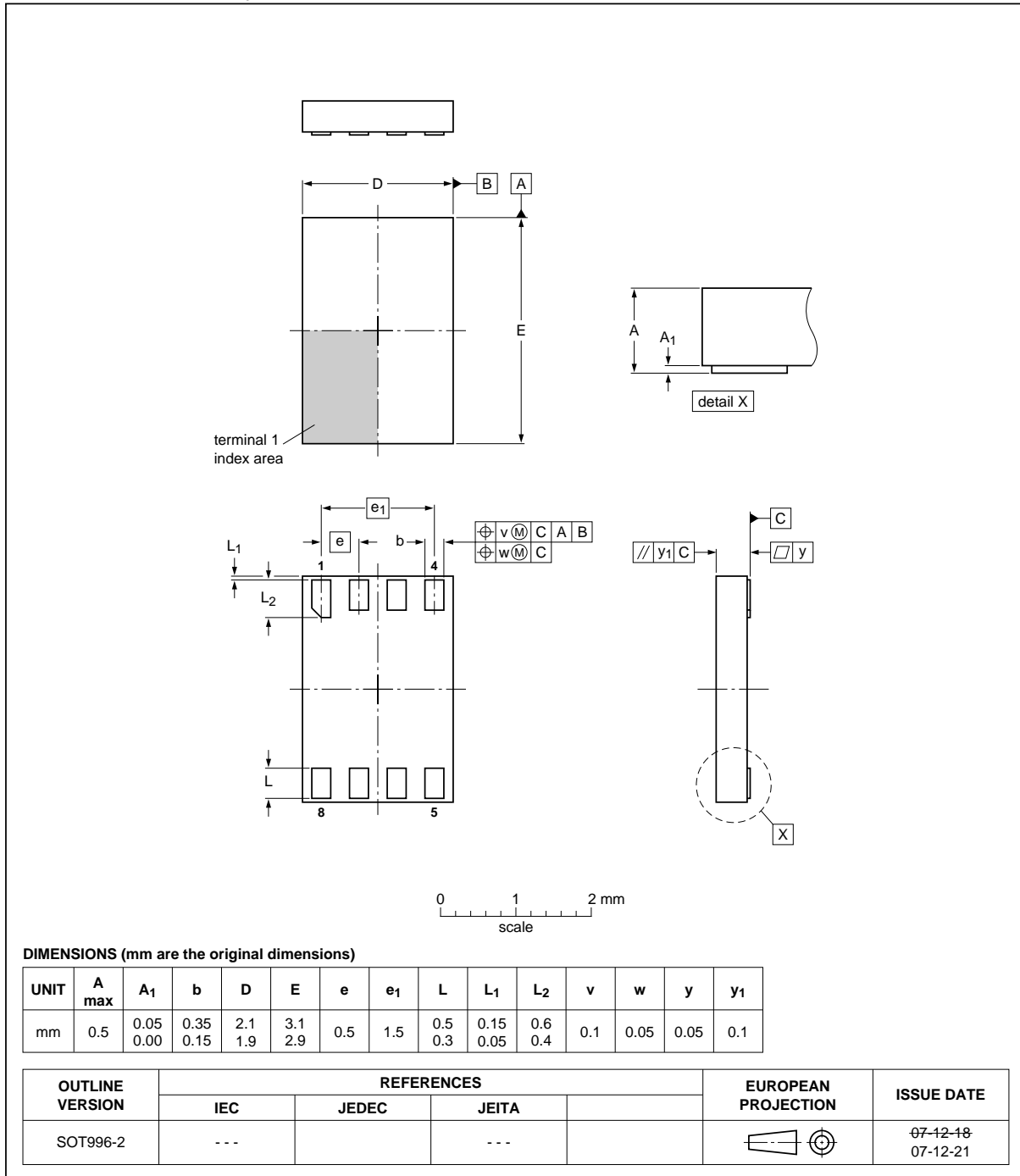


Fig 11. Package outline SOT996-2 (XSON8U)

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G126 v.6	20111108	Product data sheet	-	74AHC_AHCT2G126 v.5
Modifications:	<ul style="list-style-type: none"> <li>Legal pages updated.</li> </ul>			
74AHC_AHCT2G126 v.5	20110324	Product data sheet	-	74AHC_AHCT2G126 v.4
74AHC_AHCT2G126 v.4	20090427	Product data sheet	-	74AHC_AHCT2G126 v.3
74AHC_AHCT2G126 v.3	20090115	Product data sheet	-	74AHC_AHCT2G126 v.2
74AHC_AHCT2G126 v.2	20040921	Product data sheet	-	74AHC_AHCT2G126 v.1
74AHC_AHCT2G126 v.1	20040113	Product specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

### 16.3 Disclaimers

**Limited warranty and liability** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or

malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

**Terms and conditions of commercial sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Non-automotive qualified products** — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

## 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

## 18. Contents

---

<b>1</b>	<b>General description</b> .....	<b>1</b>
<b>2</b>	<b>Features and benefits</b> .....	<b>1</b>
<b>3</b>	<b>Ordering information</b> .....	<b>1</b>
<b>4</b>	<b>Marking</b> .....	<b>2</b>
<b>5</b>	<b>Functional diagram</b> .....	<b>2</b>
<b>6</b>	<b>Pinning information</b> .....	<b>2</b>
6.1	Pinning .....	2
6.2	Pin description .....	3
<b>7</b>	<b>Functional description</b> .....	<b>3</b>
<b>8</b>	<b>Limiting values</b> .....	<b>3</b>
<b>9</b>	<b>Recommended operating conditions</b> .....	<b>4</b>
<b>10</b>	<b>Static characteristics</b> .....	<b>4</b>
<b>11</b>	<b>Dynamic characteristics</b> .....	<b>5</b>
<b>12</b>	<b>Waveforms</b> .....	<b>7</b>
<b>13</b>	<b>Package outline</b> .....	<b>10</b>
<b>14</b>	<b>Abbreviations</b> .....	<b>13</b>
<b>15</b>	<b>Revision history</b> .....	<b>13</b>
<b>16</b>	<b>Legal information</b> .....	<b>14</b>
16.1	Data sheet status .....	14
16.2	Definitions .....	14
16.3	Disclaimers .....	14
16.4	Trademarks .....	15
<b>17</b>	<b>Contact information</b> .....	<b>15</b>
<b>18</b>	<b>Contents</b> .....	<b>16</b>

---

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2011.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

Date of release: 8 November 2011

Document identifier: 74AHC\_AHCT2G126